# Effect of Charged Clusters on the Diffusion of Impurity Atoms in Silicon Crystals

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**Abstract:** An equation of diffusion of impurity atoms in silicon crystals has been obtained, based on which the influence of charged clusters in a silicon crystal on the process of impurity transfer can be determined. It is shown that a characteristic feature of this effect is the appearance of an additional flux of impurity atoms, which is capable of leading to impurity segregation.

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